

FIG. 1

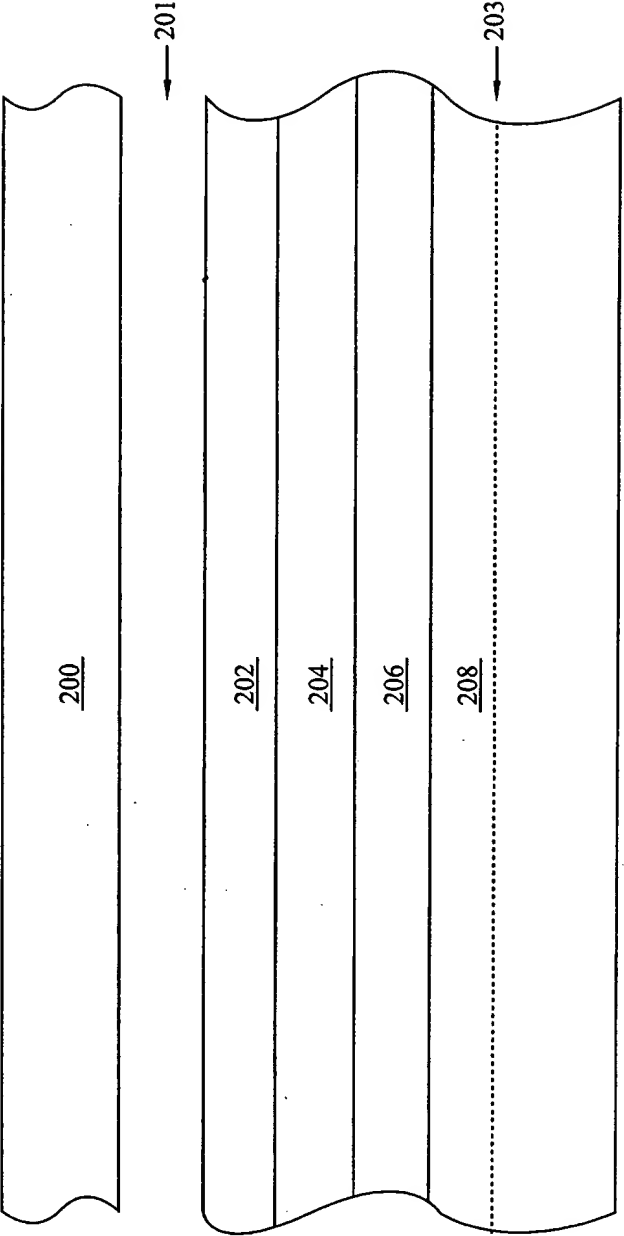


FIG. 2

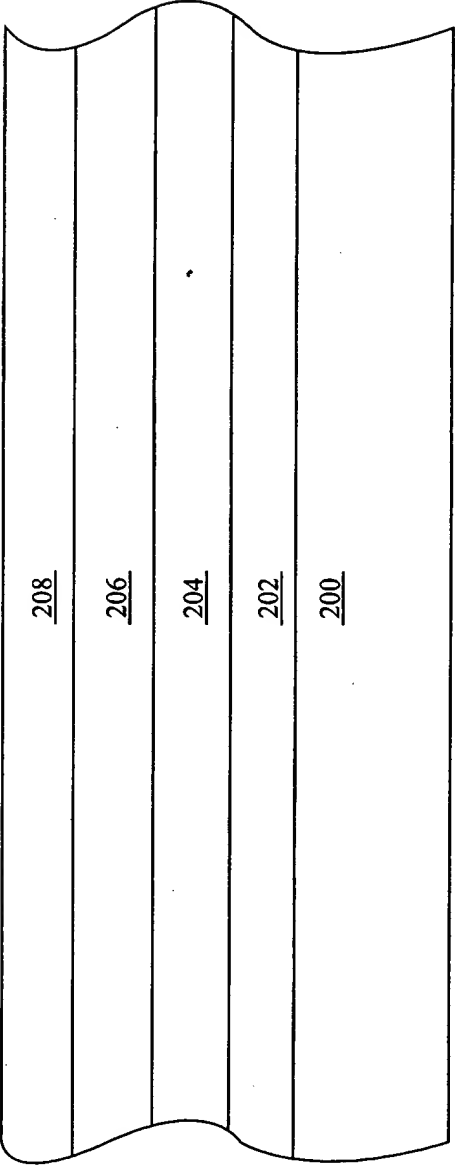


FIG. 3

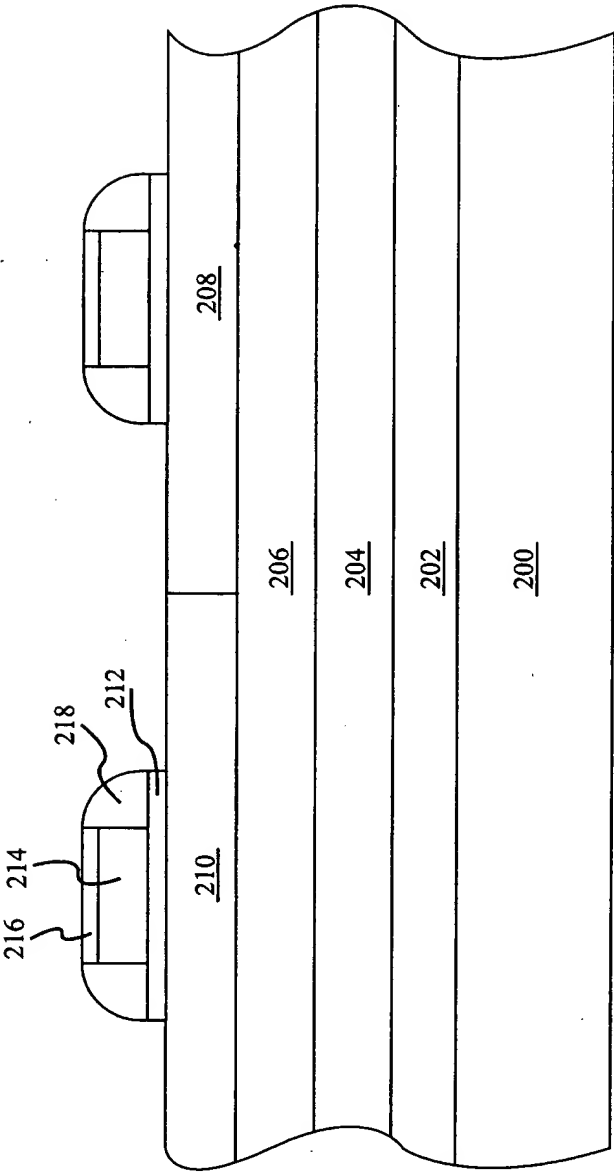


FIG. 4

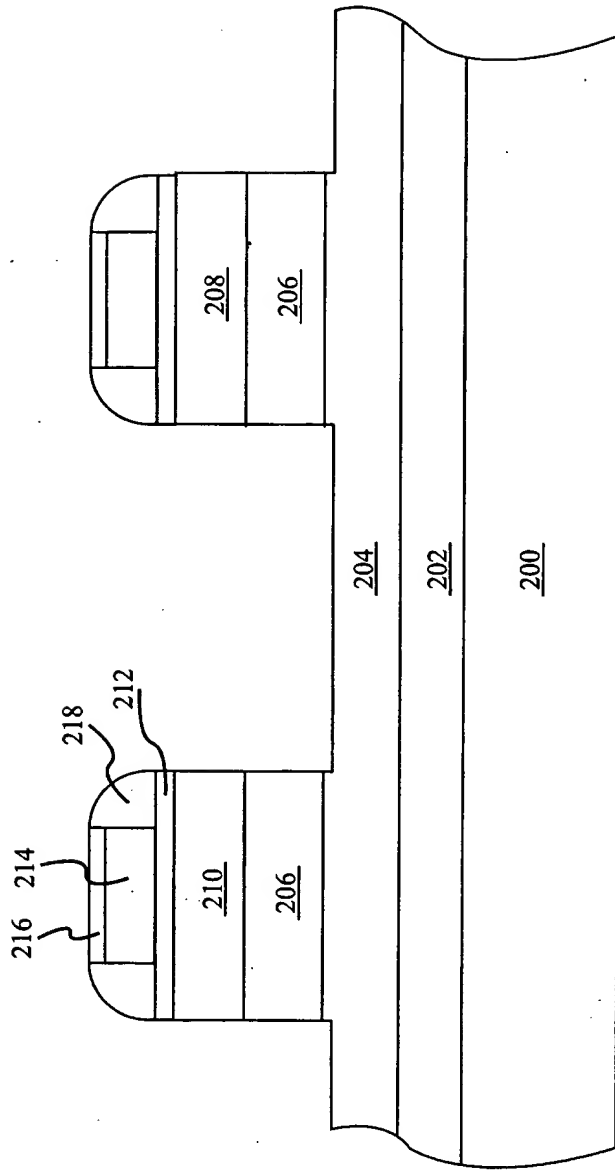


FIG. 5

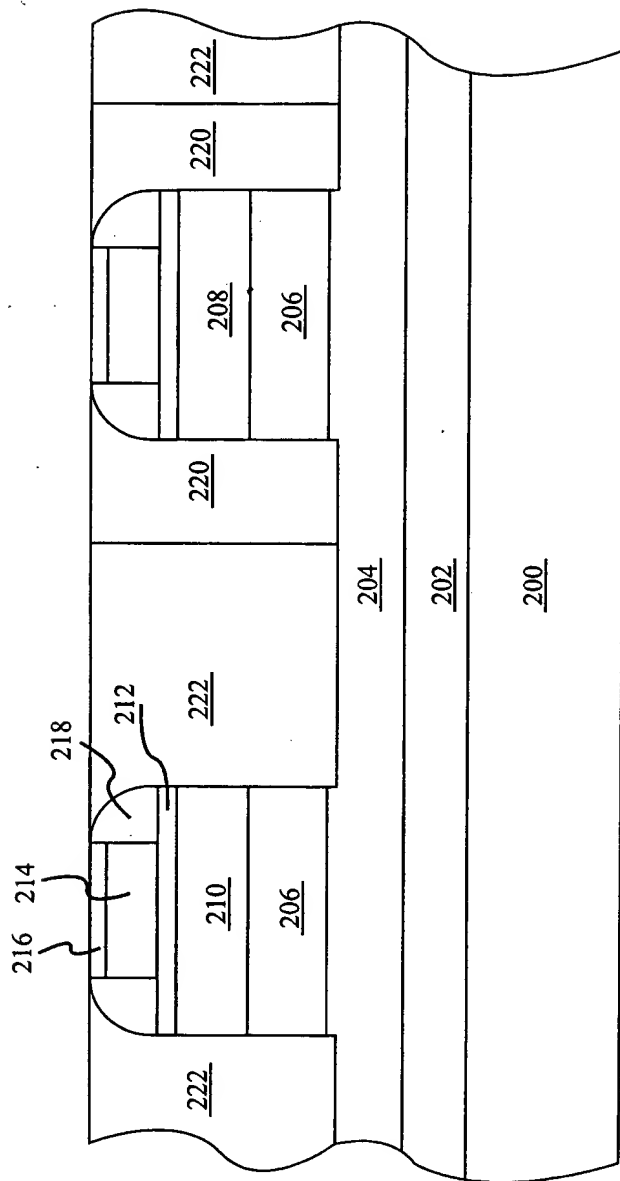


FIG. 6

FIG. 7 is a cross-sectional view of a device 200, taken along line A-A of FIG. 6. The device 200 includes a substrate 202, a gate stack 204, a gate electrode 206, a gate insulator 208, a gate spacer 210, a gate contact 212, a gate pad 214, a gate opening 216, a gate trench 218, a gate sidewall 220, a gate top 222, a gate bottom 224, a gate side 226, a gate end 228, a gate corner 230, a gate edge 232, a gate face 234, a gate surface 236, a gate volume 238, a gate area 240, a gate perimeter 242, a gate boundary 244, a gate interface 246, a gate junction 248, a gate transition 250, a gate feature 252, a gate structure 254, a gate element 256, a gate component 258, a gate part 260, a gate portion 262, a gate section 264, a gate segment 266, a gate piece 268, a gate fragment 270, a gate piece 272, a gate part 274, a gate portion 276, a gate section 278, a gate segment 280, a gate piece 282, a gate fragment 284, a gate piece 286, a gate part 288, a gate portion 290, a gate section 292, a gate segment 294, a gate piece 296, a gate fragment 298, a gate piece 300.

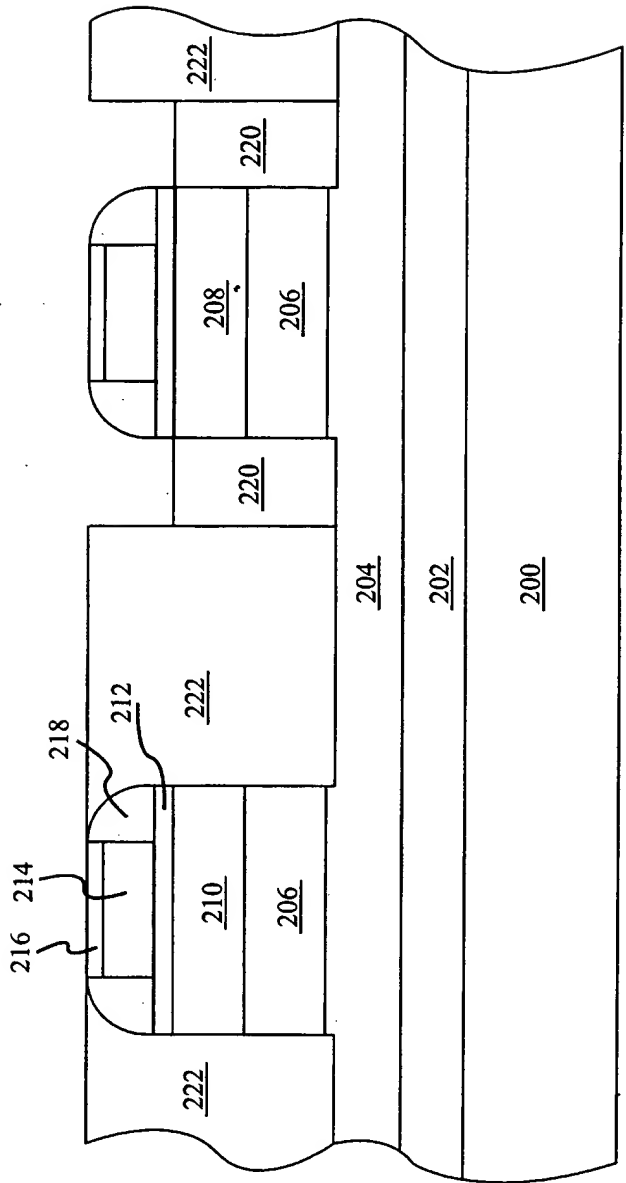


FIG. 7

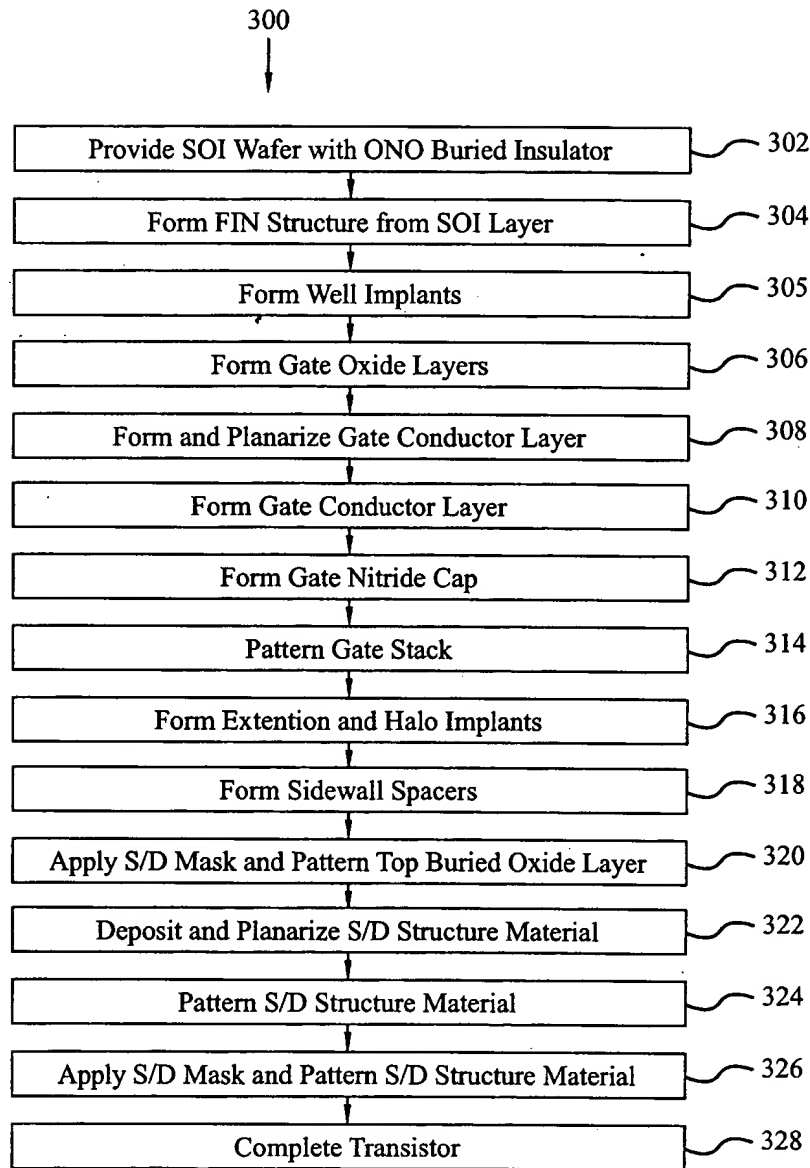


FIG. 8



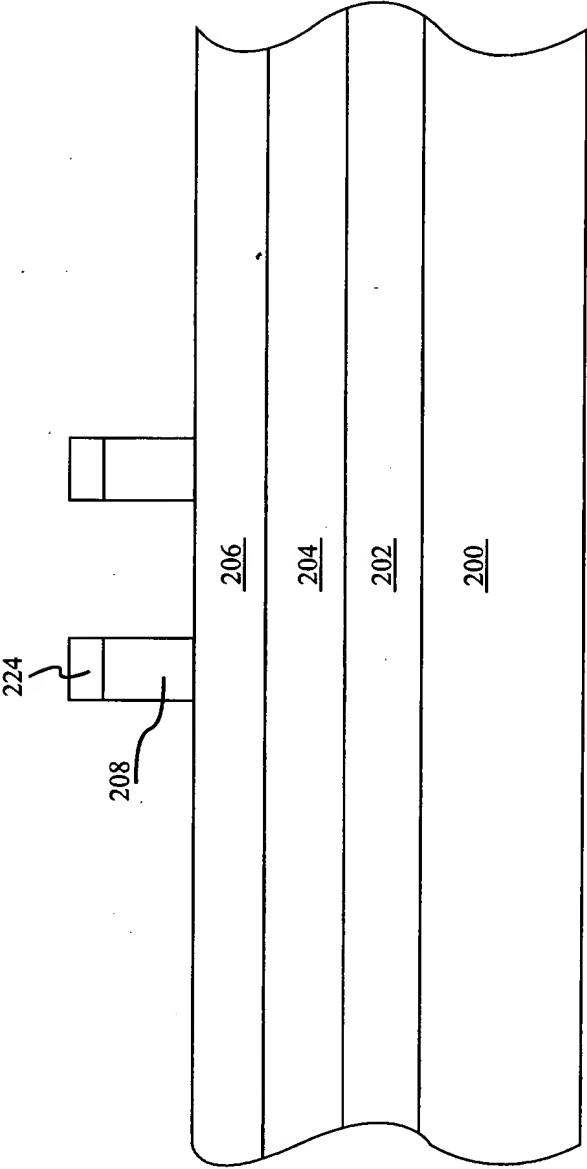


FIG. 9

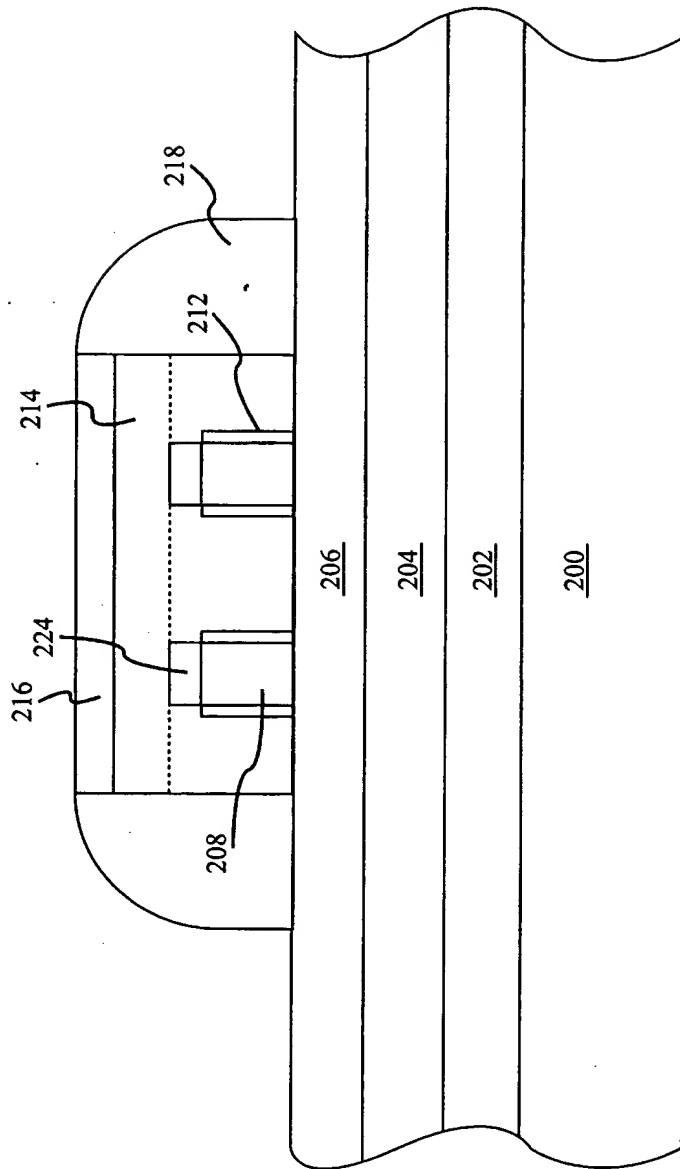


FIG. 10

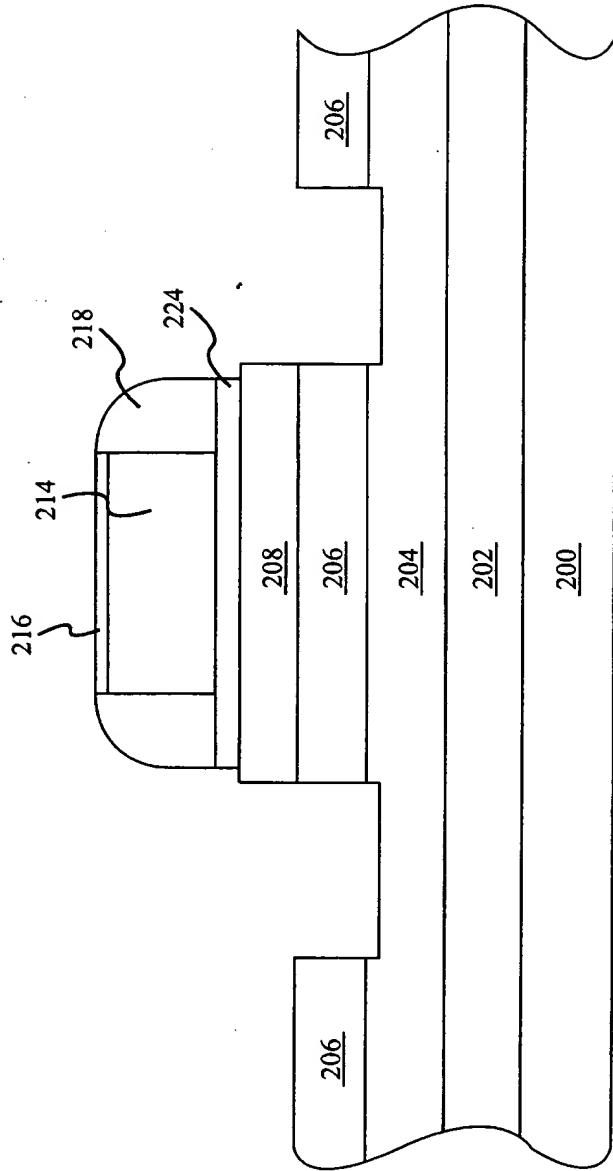


FIG. 11

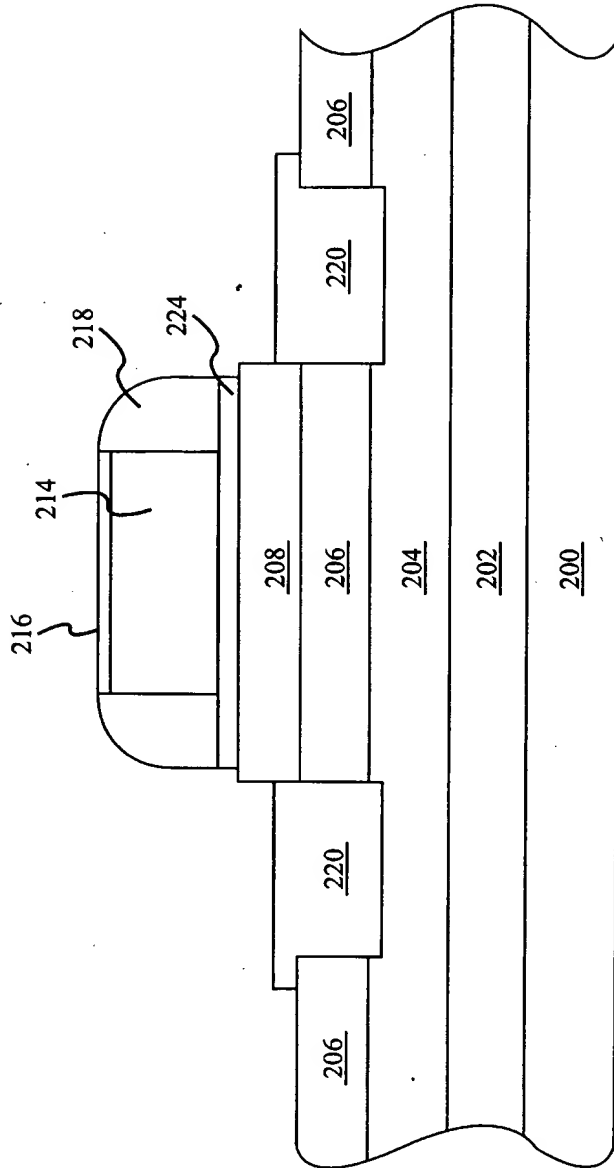


FIG. 12

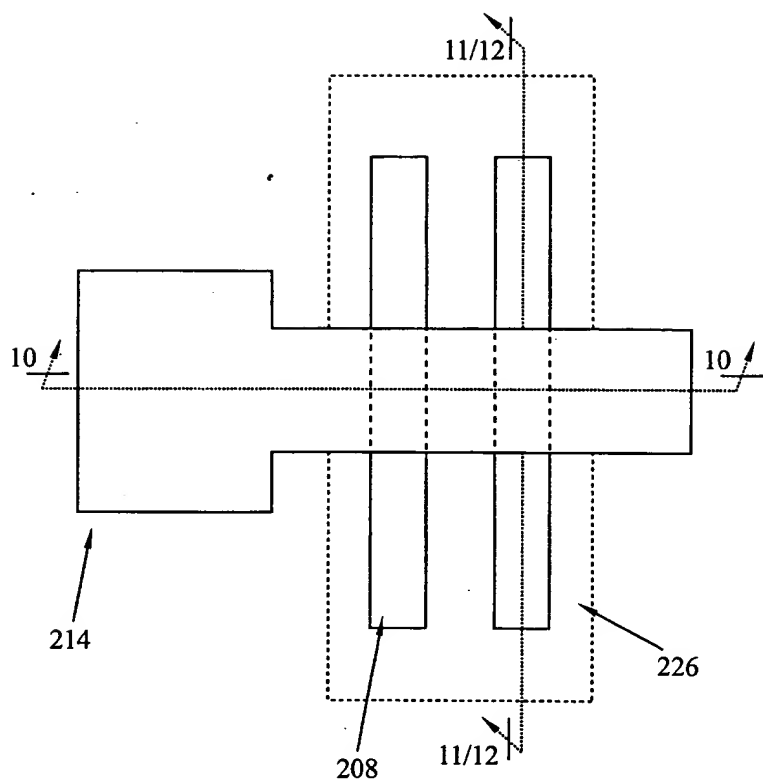


FIG. 13